

## Features

- 650-Volt Schottky Rectifier
- Optimized for PFC Boost Diode Application
- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Extremely Fast Switching
- Positive Temperature Coefficient on  $V_F$

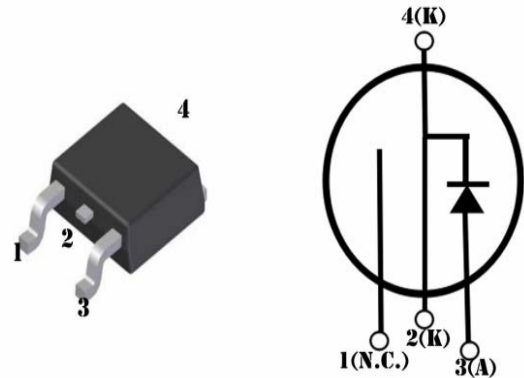
## Benefits

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

## Applications

- Switch Mode Power Supplies (SMPS)
- Boost diodes in PFC or DC/DC stages
- Free Wheeling Diodes in Inverter stages
- AC/DC converters

## Package



## Maximum Ratings ( $T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
$V_{RRM}$	Repetitive Peak Reverse Voltage	650	V		
$V_{RSM}$	Surge Peak Reverse Voltage	650	V		
$V_{DC}$	DC Blocking Voltage	650	V		
$I_F$	Continuous Forward Current	13.5 6 4	A	$T_C=25^\circ\text{C}$ $T_C=135^\circ\text{C}$ $T_C=155^\circ\text{C}$	Fig. 3
$I_{FRM}$	Repetitive Peak Forward Surge Current	17 12	A	$T_C=25^\circ\text{C}$ , $t_p = 10$ ms, Half Sine Wave $T_C=110^\circ\text{C}$ , $t_p = 10$ ms, Half Sine Wave	
$I_{FSM}$	Non-Repetitive Peak Forward Surge Current	25 19	A	$T_C=25^\circ\text{C}$ , $t_p = 10$ ms, Half Sine Wave $T_C=110^\circ\text{C}$ , $t_p = 10$ ms, Half Sine Wave	Fig. 8
$I_{F,Max}$	Non-Repetitive Peak Forward Surge Current	220 160	A	$T_C=25^\circ\text{C}$ , $t_p = 10$ $\mu\text{s}$ , Pulse $T_C=110^\circ\text{C}$ , $t_p = 10$ $\mu\text{s}$ , Pulse	Fig. 8
$P_{tot}$	Power Dissipation	52 22.5	W	$T_C=25^\circ\text{C}$ $T_C=110^\circ\text{C}$	Fig. 4
dV/dt	Diode dV/dt ruggedness	200	V/ns	$V_R=0-650\text{V}$	
$\int i^2 dt$	$i^2t$ value	3.1 1.8	$\text{A}^2\text{s}$	$T_C=25^\circ\text{C}$ , $t_p=10$ ms $T_C=110^\circ\text{C}$ , $t_p=10$ ms	
$T_J, T_{stg}$	Operating Junction and Storage Temperature	-55 to +175	$^\circ\text{C}$		

Electrical Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
$V_F$	Forward Voltage	1.4 1.7	1.7 2.4	V	$I_F = 4\text{ A } T_J = 25^\circ\text{C}$ $I_F = 4\text{ A } T_J = 175^\circ\text{C}$	Fig. 1
$I_R$	Reverse Current	5 10	25 100	$\mu\text{A}$	$V_R = 650\text{ V } T_J = 25^\circ\text{C}$ $V_R = 650\text{ V } T_J = 175^\circ\text{C}$	Fig. 2
$Q_C$	Total Capacitive Charge	10		nC	$V_R = 400\text{ V}, I_F = 4\text{ A}$ $di/dt = 500\text{ A}/\mu\text{s}$ $T_J = 25^\circ\text{C}$	Fig. 5
C	Total Capacitance	231 18.5 15		pF	$V_R = 0\text{ V}, T_J = 25^\circ\text{C}, f = 1\text{ MHz}$ $V_R = 200\text{ V}, T_J = 25^\circ\text{C}, f = 1\text{ MHz}$ $V_R = 400\text{ V}, T_J = 25^\circ\text{C}, f = 1\text{ MHz}$	Fig. 6
$E_C$	Capacitance Stored Energy	1.4		$\mu\text{J}$	$V_R = 400\text{ V}$	Fig. 7

Note: This is a majority carrier diode, so there is no reverse recovery charge.

Thermal Characteristics

Symbol	Parameter	Typ.	Unit	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	2.9	$^\circ\text{C}/\text{W}$	Fig. 9

Typical Performance

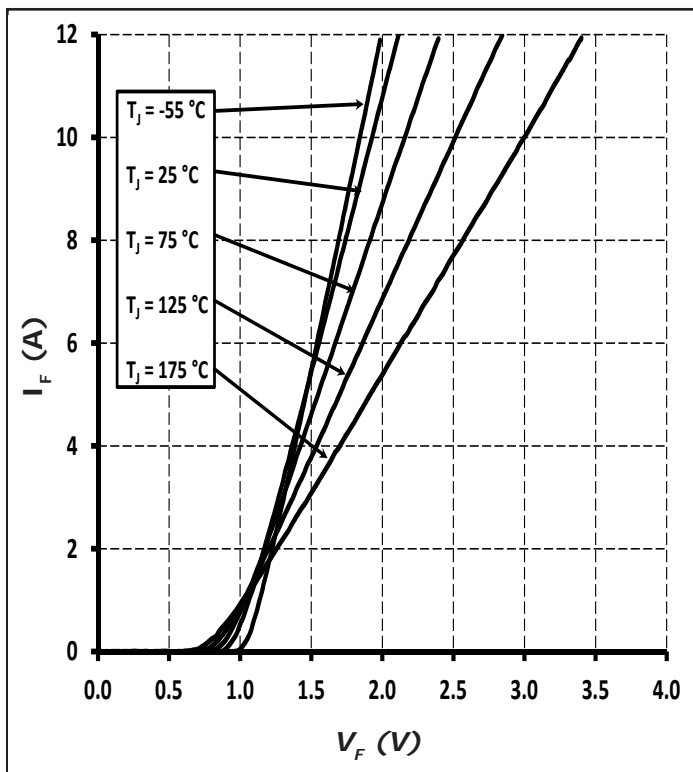


Figure 1. Forward Characteristics

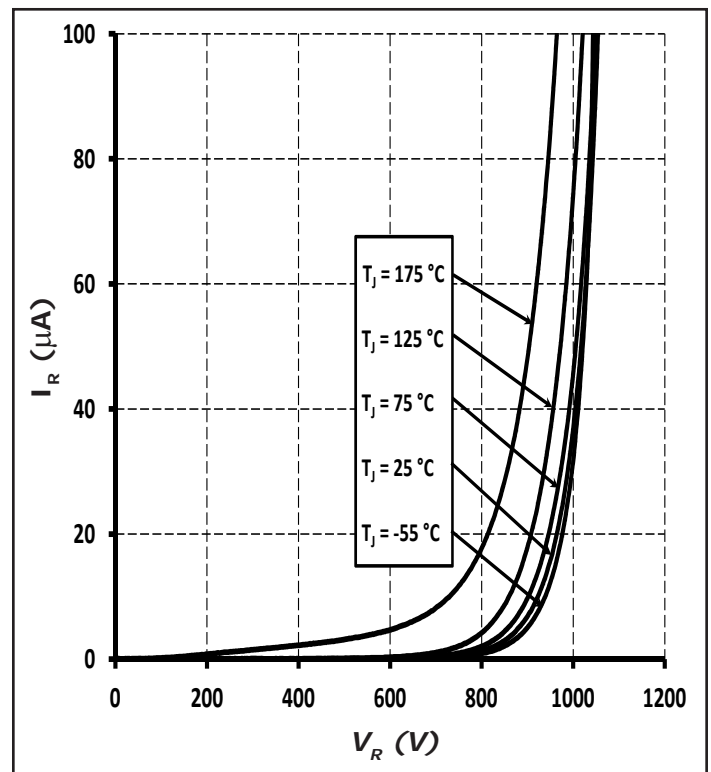


Figure 2. Reverse Characteristics

Typical Performance

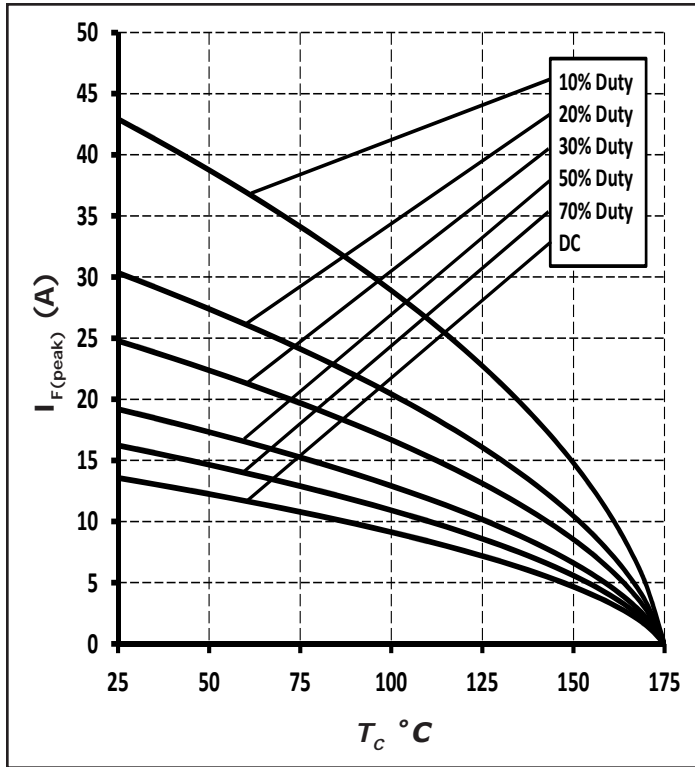


Figure 3. Current Derating

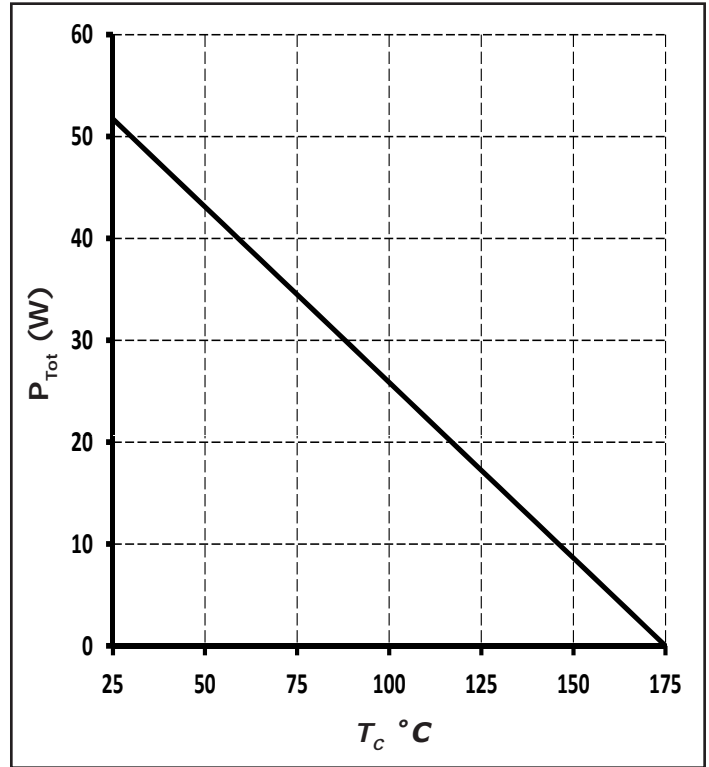


Figure 4. Power Derating

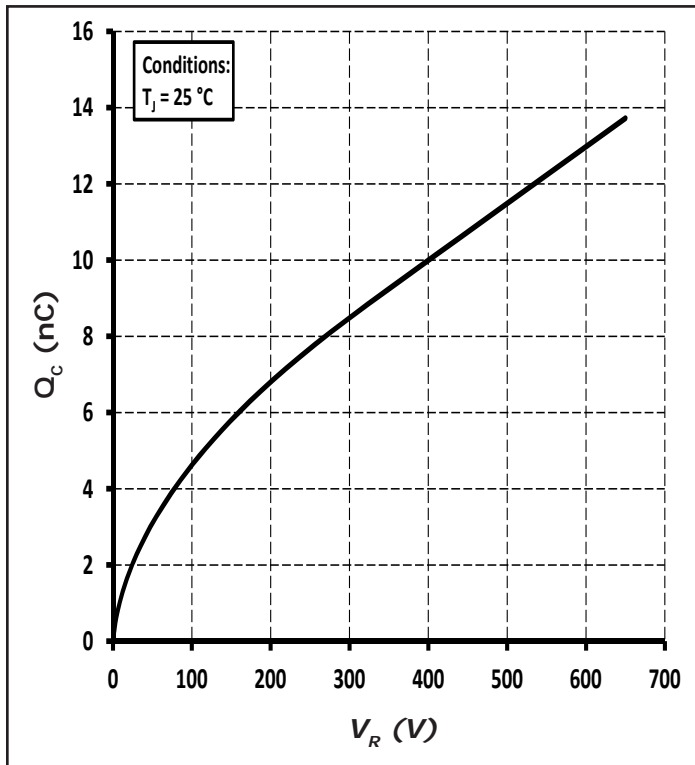


Figure 5. Total Capacitance Charge vs. Reverse Voltage

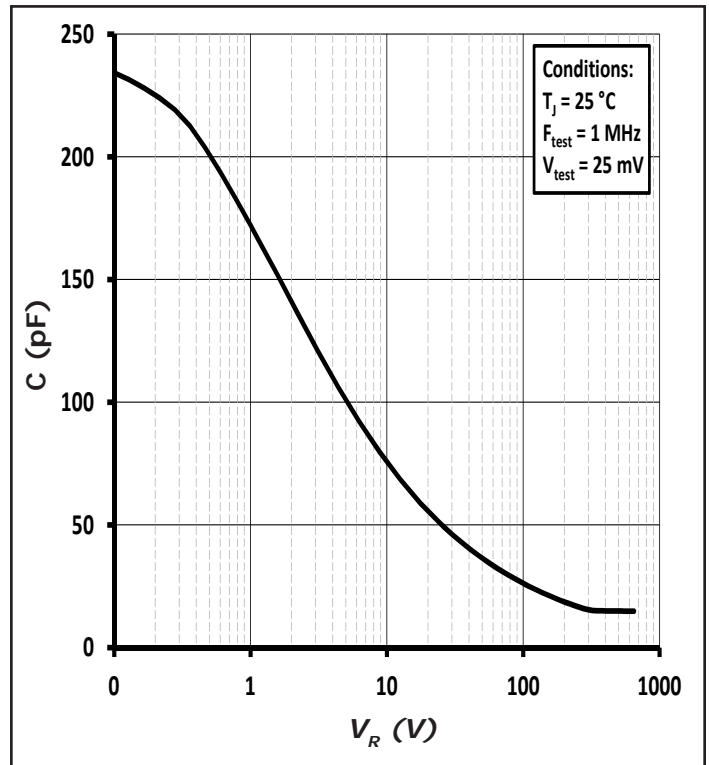


Figure 6. Capacitance vs. Reverse Voltage

Typical Performance

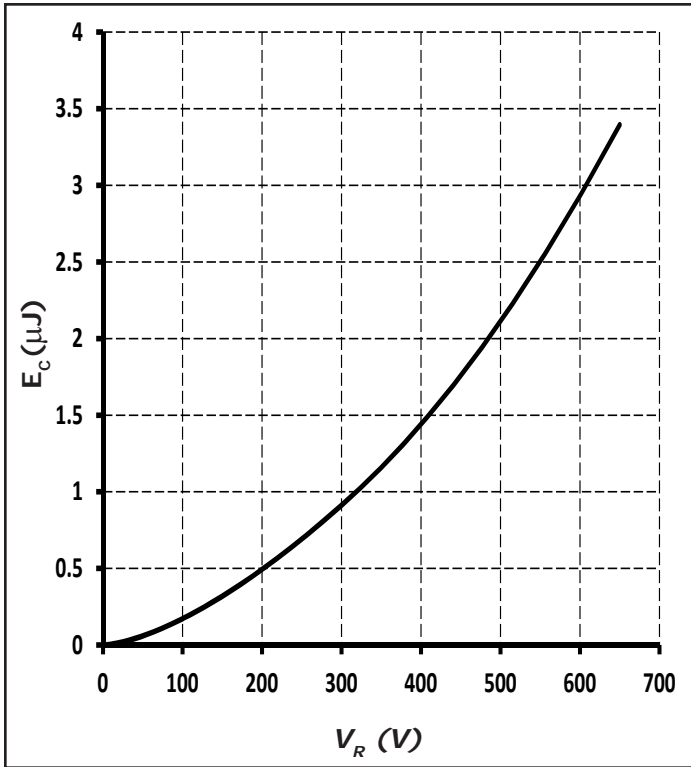


Figure 7. Capacitance Stored Energy

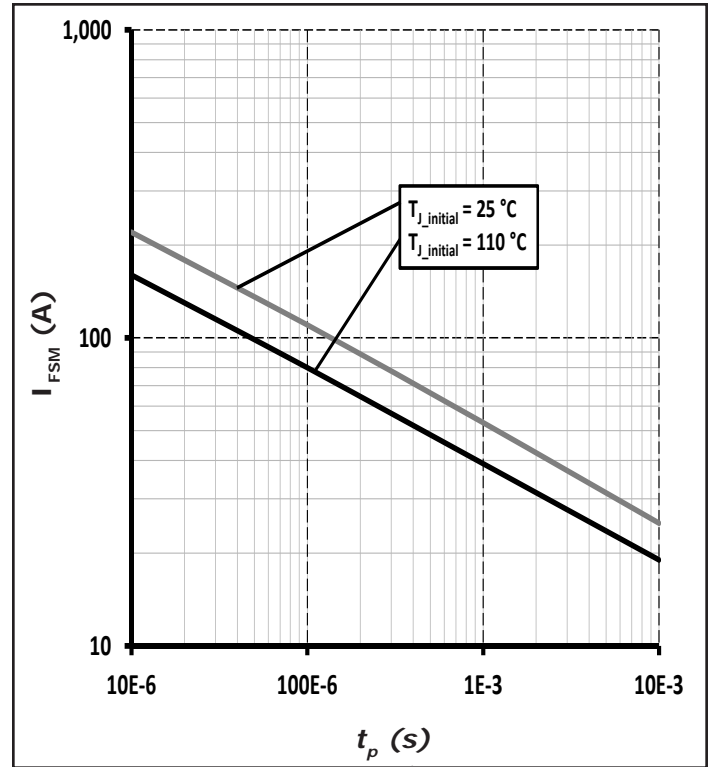


Figure 8. Non-repetitive peak forward surge current versus pulse duration (sinusoidal waveform)

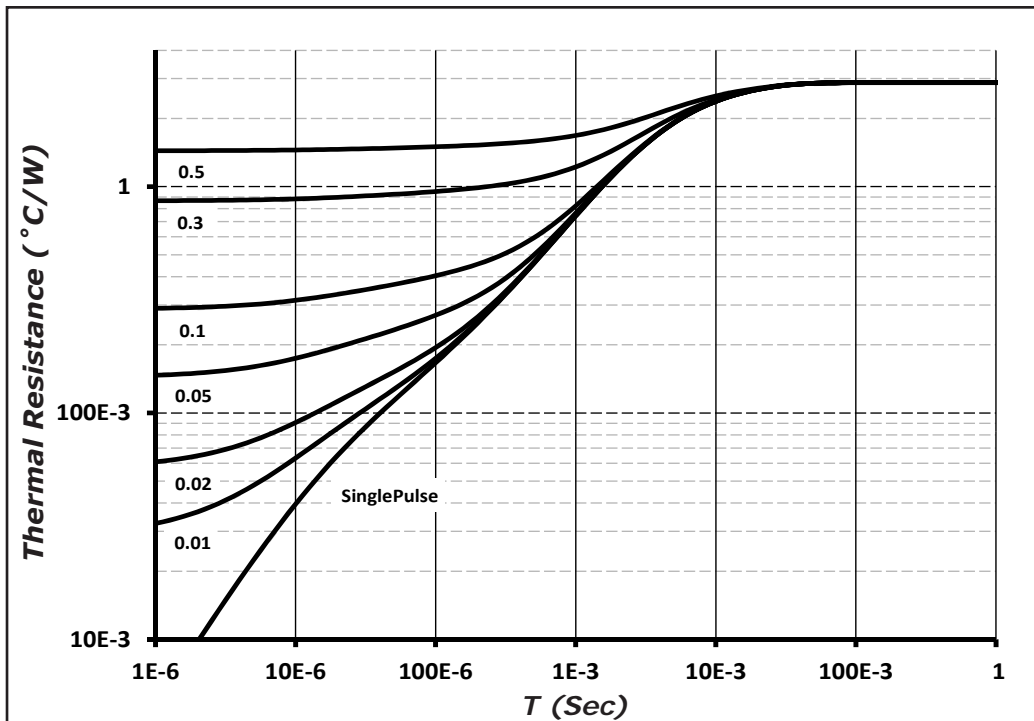
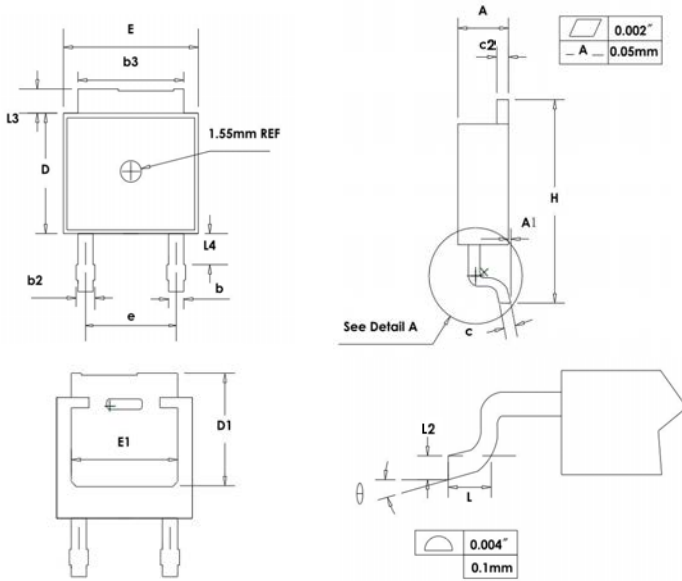


Figure 9. Transient Thermal Impedance

**Package Dimensions**

Package TO-252-2



SYMBOL	MILLIMETERS	
	MIN	MAX
A	2.159	2.413
A1	0	0.13
b	0.64	0.89
b2	0.653	1.143
b3	5.004	5.6
c	0.457	0.61
c2	0.457	0.864
D	5.867	6.248
D1	5.21	-
E	6.35	7.341
E1	4.32	-
e	4.58 BSC	
H	9.65	10.414
L	1.106	1.78
L2	0.51 BSC	
L3	0.889	1.27
L4	0.64	1.01
θ	0°	8°